

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE4080D uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

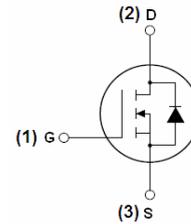
- $V_{DS} = 40V, I_D = 80A$
 $R_{DS(ON)} < 6.5m\Omega @ V_{GS} = 10V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- PWM
- Load Switching

100% UIS TESTED!

100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment



TO-263-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4080D	NCE4080D	TO-263-2L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	80	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	56	A
Pulsed Drain Current	I_{DM}	350	A
Maximum Power Dissipation	P_D	90	W
Derating factor		0.6	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	670	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.67	$^{\circ}C/W$
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Electrical Characteristics ($T_C=25^{\circ}C$ unless otherwise noted)

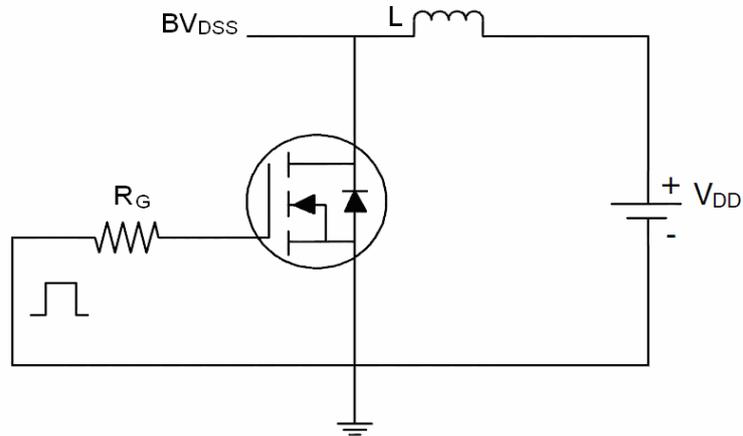
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40	45	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	5.3	6.5	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=20A$	15	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	4010	-	PF
Output Capacitance	C_{oss}		-	750	-	PF
Reverse Transfer Capacitance	C_{rss}		-	390	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, R_L=1\Omega$ $V_{GS}=10V, R_G=3\Omega$	-	11	-	nS
Turn-on Rise Time	t_r		-	10	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	38	-	nS
Turn-Off Fall Time	t_f		-	11	-	nS
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=20A,$ $V_{GS}=10V$	-	50	-	nC
Gate-Source Charge	Q_{gs}		-	12	-	nC
Gate-Drain Charge	Q_{gd}		-	13	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=10A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	80	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}C, I_F = 20A$ $di/dt = 100A/\mu s$ ^(Note 3)	-	33	-	nS
Reverse Recovery Charge	Q_{rr}		-	34	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

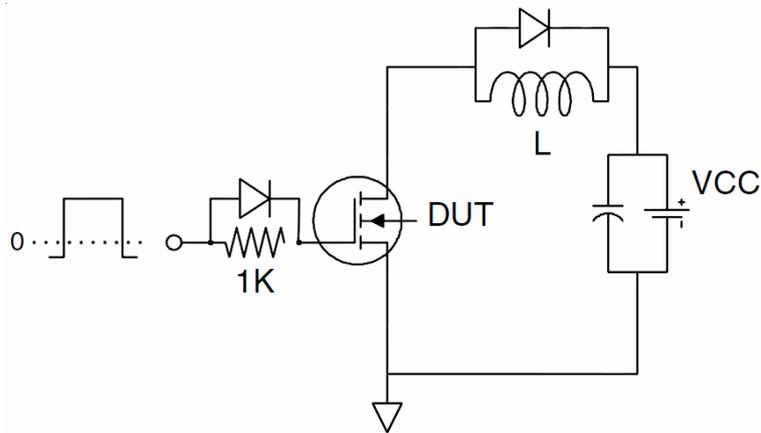
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : $T_J=25^{\circ}C, V_{DD}=20V, V_G=10V, L=1mH, R_g=25\Omega, I_{AS}=36A$

Test circuit

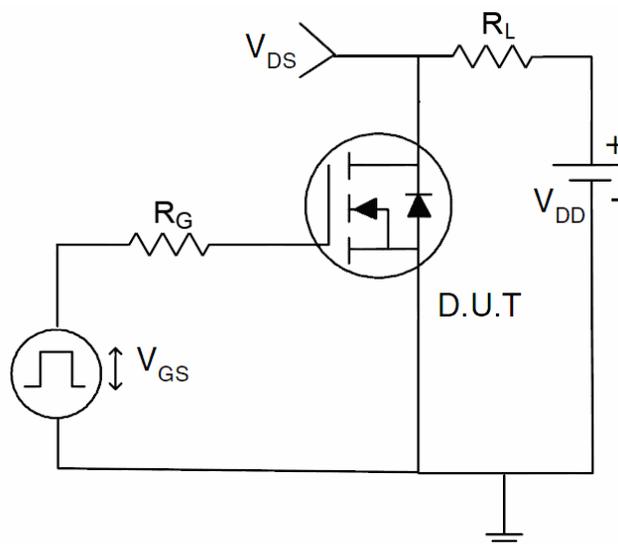
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

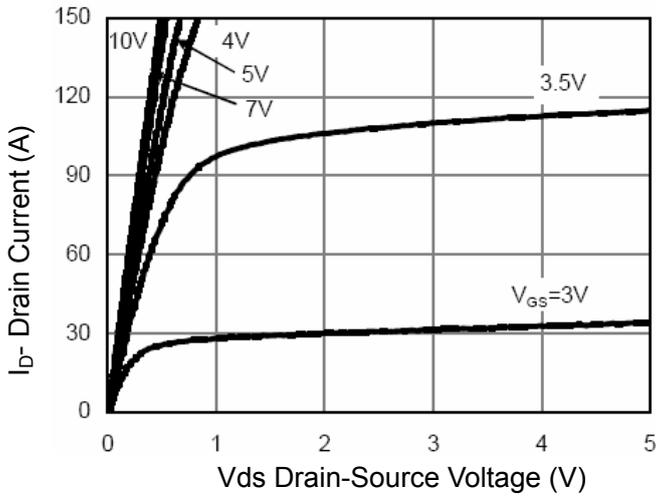


Figure 1 Output Characteristics

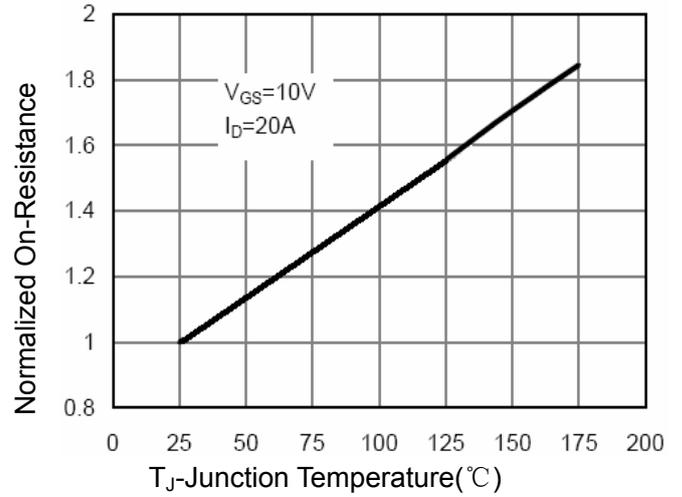


Figure 4 R_{dson} -Junction Temperature

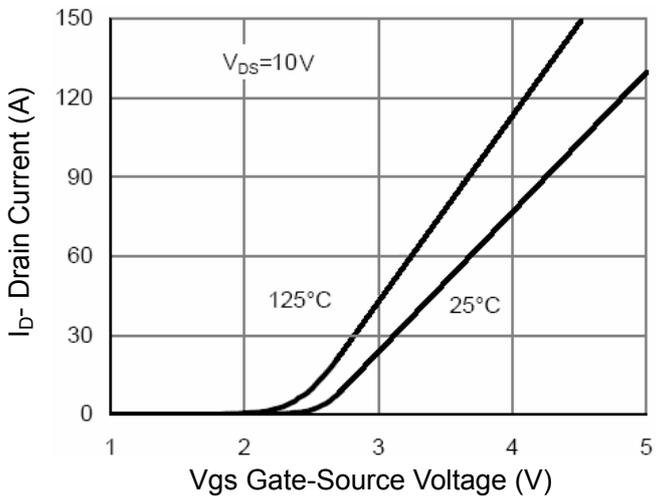


Figure 2 Transfer Characteristics

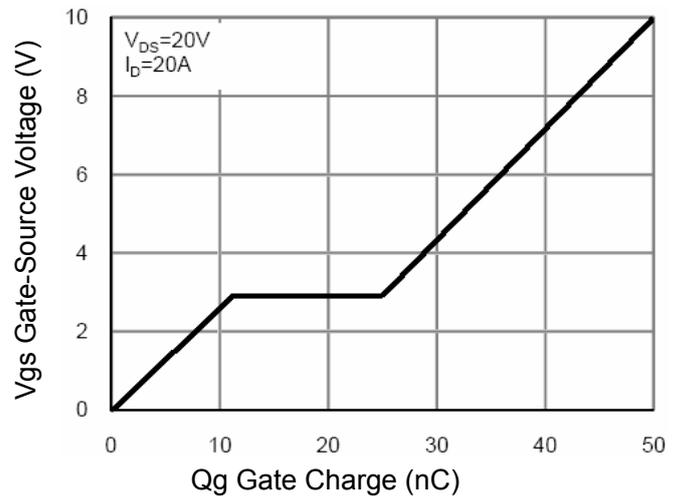


Figure 5 Gate Charge

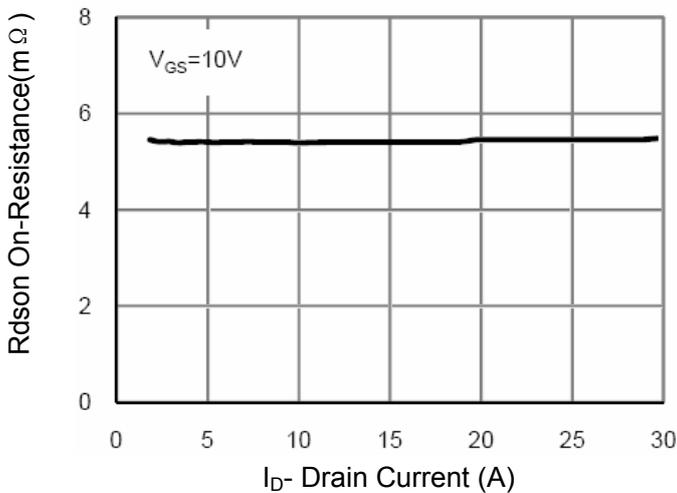


Figure 3 R_{dson} - Drain Current

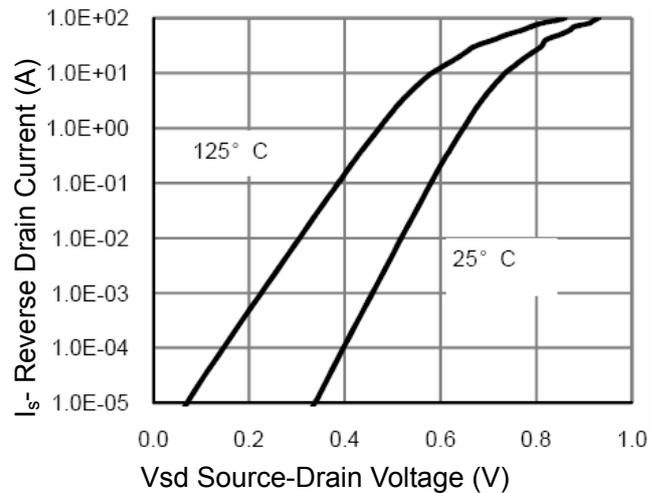


Figure 6 Source- Drain Diode Forward

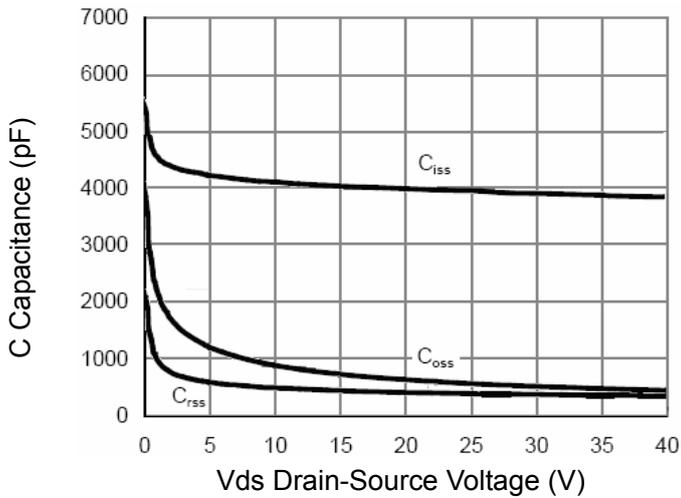


Figure 7 Capacitance vs Vds

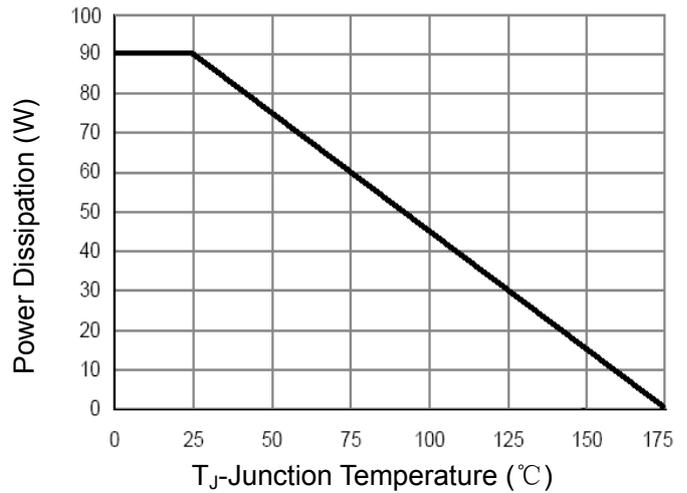


Figure 9 Power De-rating

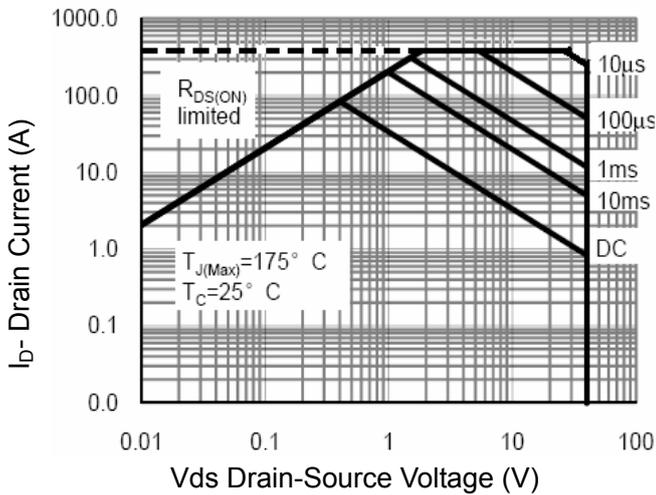


Figure 8 Safe Operation Area

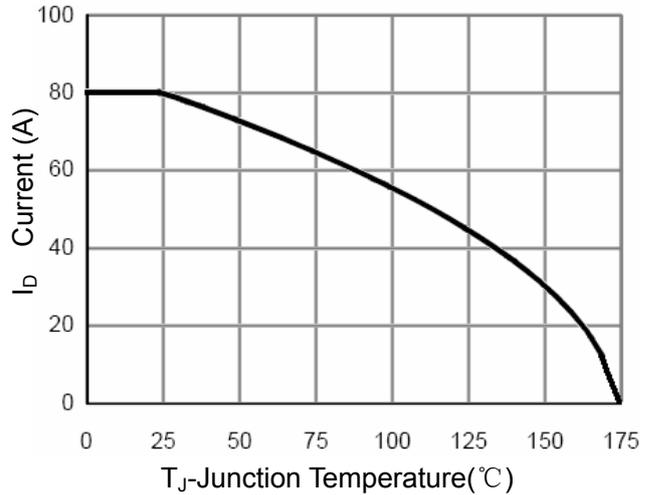


Figure 10 Id Current- Junction Temperature

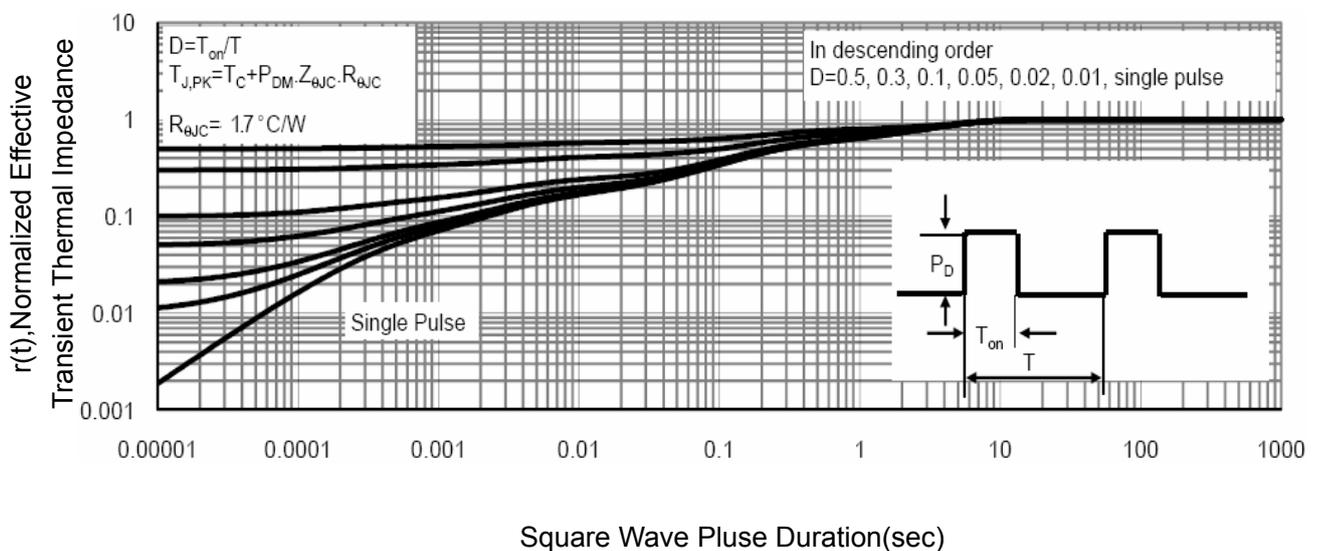
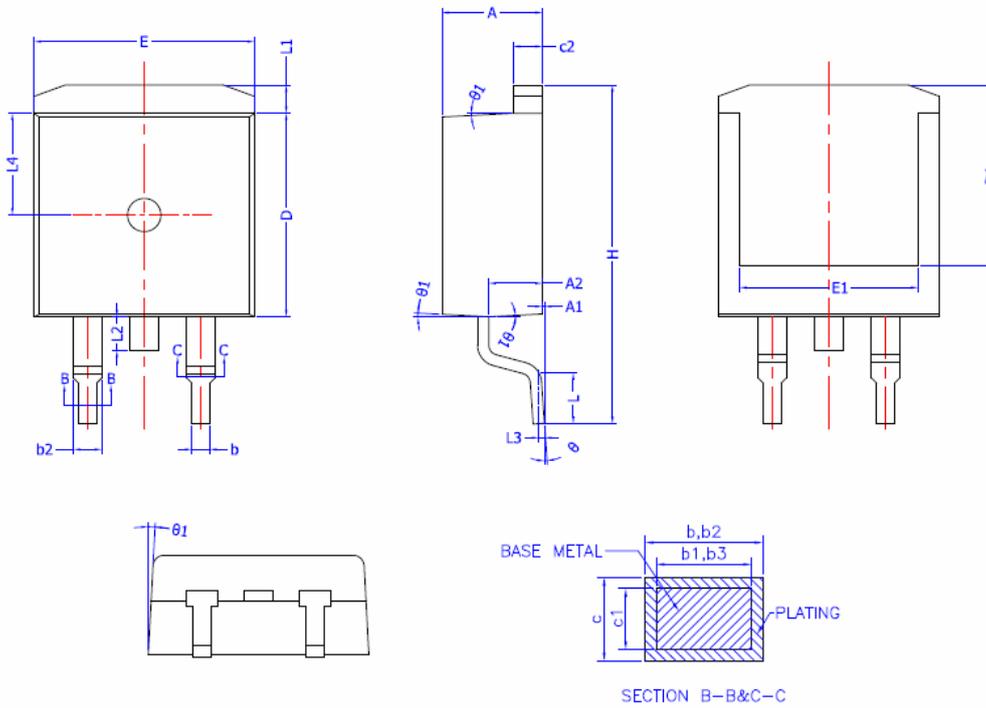


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	0	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	—	0.89
b1	0.75	0.80	0.85
b2	1.23	—	1.37
b3	1.22	1.27	1.32
c	0.47	—	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	—	—
E	9.80	9.90	10.00
E1	7.80	—	—
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	—	—	1.75
L3	0.25BSC		
L4	4.60 REF		
θ	0°	—	8°
θ1	1°	3°	5°

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